

ABSTRACT OF THE DISCLOSURE

Heat diffusion preventing film is formed on the cleavage plane of a semiconductor laser, and thin film comprising a low melting point material, such as indium, is formed on top on the heat diffusion preventing film. When irradiated by the laser light emitted from the semiconductor laser and heated, the irradiated area of the thin film changes in state from crystalline to amorphous and forms a small light transmitting area. Near field light passes through this light transmitting area. The near field light generating device of the present invention uses a simple construction as described above, and complex adjustment is not required. In addition, problems such as laser oscillation failure do not occur.

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